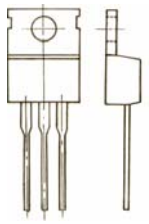
深圳市晶泰源电子有限公司

MJE2955 TRANSISTOR (PNP)

TO-220

1. BASE
2. COLLECTOTR
3. EMITTER



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FEATURES

GENERAL PURPOSE AND SWITCHING APPLICATIONS.

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-70	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-10	A
P_C	Collector Power Dissipation	2	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55-150	℃

ELECTRICAL CHARACTERISTICS(Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10mA, I_E=0	-70			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-200mA, I_B=0	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10mA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-70V, I_E=0			-1	mA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-5	mA
DC current gain	$h_{FE(1)}$ *	V_{CE}=-4V, I_C=-4A	20		100	
	$h_{FE(2)}$ *	V_{CE}=-4V, I_C=-10A	5			
Collector-emitter saturation voltage	$V_{CE(sat)}$ *	I_C=-4A, I_B=-0.4A			-1.1	V
	$V_{CE(sat)}$ *	I_C=-10A, I_B=-3.3A			-8	V
Base-emitter voltage	V_{BE}*	V_{CE}=-4V, I_C=-4A			-1.8	V
Transition frequency	f_T	V_{CE}=-10V, I_C=-0.5A	2			MHz

Note:*Pulse test: t_p≤300μS, δ≤0.02.

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